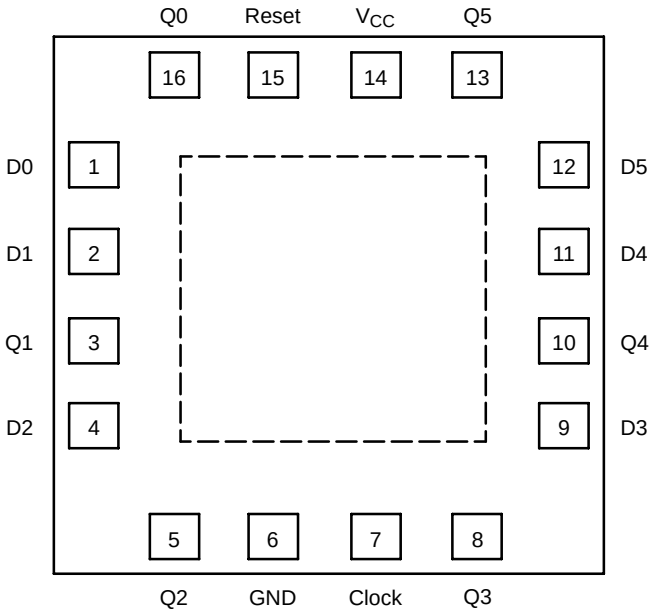
NLSF1174

Hex D Flip-Flop with Common Clock and Reset

This device consists of six D flip−flops with common Clock and Reset inputs. Each flip−flop is loaded with a low−to−high transition of the Clock input. Reset is asynchronous and active low. All inputs/outputs are standard CMOS compatible.

Features

- Output Drive Compatibility: 10 LSTTL Loads
- Outputs Directly Interface to CMOS
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- MSL Level 1
- Chip Complexity: 162 FET
- Pb−Free Package is Available*



Center pad on bottom may be connected to V_{CC} of device. This pad must be isolated or connected to V_{CC}.

Figure 1. PIN ASSIGNMENT (Top View)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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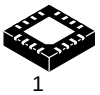
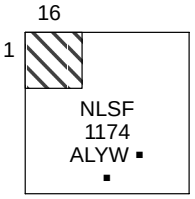


QFN−16
MN SUFFIX
CASE 485G

MARKING DIAGRAM



NLSF1174 = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

Inputs			Output
Reset	**Clock**	**D**	**Q**
L	X	X	L
H	↑	H	H
H	↑	L	L
H	L	X	No Change
H	↓	X	No Change

ORDERING INFORMATION

Device	Package	Shipping†
NLSF1174MNR2	QFN−16	3000 / Tape & Reel
NLSF1174MNR2G	QFN−16 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

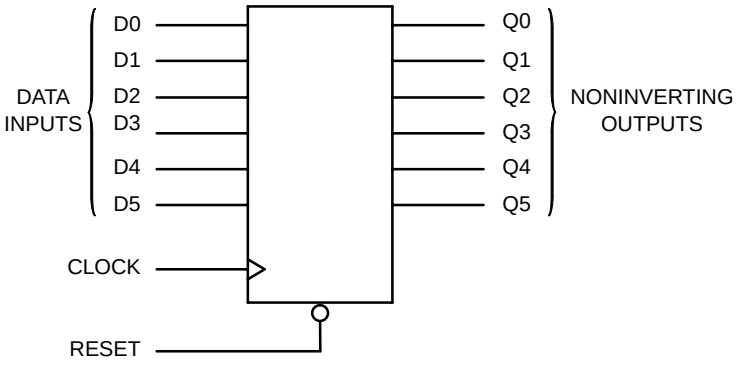


Figure 2. LOGIC DIAGRAM

DESIGN/VALUE TABLE

Design Criteria	Value	Unit
Internal Gate Count*	40.5	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	pJ

*Equivalent to a two−input NAND gate.

MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
DC Supply Voltage	(Referenced to GND)	V_{CC}	−0.5 to +7.0	V
DC Input Voltage	(Referenced to GND)	V_{IN}	−1.5 to V_{CC} +1.5	V
DC Output Voltage	(Referenced to GND) (Note 1)	V_{OUT}	−0.5 to V_{CC} +0.5	V
DC Input Current, per Pin		I_{IN}	±20	mA
DC Output Current, per Pin		I_{OUT}	±25	mA
DC Supply Current, V_{CC} and GND Pins		I_{CC}	±50	mA
Storage Temperature Range		T_{STG}	−65 to +150	°C
Lead Temperature, 1 mm from Case for 10 Seconds	PDIP, SOIC, TSSOP	T_L	260	°C
Junction Temperature Under Bias		T_J	+150	°C
Thermal Resistance	QFN	θ_{JA}	80	°C/W
Power Dissipation in Still Air at 85°C	QFN	P_D	800	mW
Moisture Sensitivity		MSL	Level 1	
Flammability Rating	Oxygen Index: 30 to 35	F_R	UL 94 V−0 @ 0.125 in	
ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	V_{ESD}	>2000 >100 >500	V
Latchup Performance	Above V_{CC} and Below GND at 85°C (Note 5)	$I_{LATCHUP}$	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I_O absolute maximum rating must be observed.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.
4. Tested to JESD22−C101−A.
5. Tested to EIA/JESD78.
6. For high frequency or heavy load considerations, see the ON Semiconductor High−Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Parameter		Symbol	Min	Max	Unit
DC Supply Voltage	(Referenced to GND)	V_{CC}	2.0	6.0	V
DC Input Voltage, Output Voltage	(Referenced to GND) (Note 7)	V_{IN}, V_{OUT}	0	V_{CC}	V
Operating Temperature, All Package Types		T_A	−55	+125	°C
Input Rise and Fall Time (Figure 4)	V_{CC} = 2.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V	t_r, t_f	0 0 0	1000 500 400	ns

7. Unused inputs may not be left open. All inputs must be tied to a high− or low−logic input voltage level.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Parameter	Test Conditions	Symbol	V_{CC} V	Guaranteed Limit			Unit
				−55°C to 25°C	≤85°C	≤125°C	
Minimum High−Level Input Voltage	V_{OUT} = 0.1 V or V_{CC} – 0.1 V $\|I_{OUT}\| \le 20$ μA	V_{IH}	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
Maximum Low−Level Input Voltage	V_{OUT} = 0.1 V or V_{CC} – 0.1 V $\|I_{OUT}\| \le 20$ μA	V_{IL}	2.0 4.5 6.0	0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V
Minimum High−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 20$ μA	V_{OH}	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 4.0$ mA $\|I_{OUT}\| \le 5.2$ mA		4.5 6.0	3.98 5.48	3.84 5.34	3.7 5.2	
Maximum Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 20$ μA	V_{OL}	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 4.0$ mA $\|I_{OUT}\| \le 5.2$ mA		4.5 6.0	0.26 0.26	0.33 0.33	0.4 0.4	
Maximum Input Leakage Current	V_{IN} = V_{CC} or GND	I_{IN}	6.0	±0.1	±1.0	±1.0	μA
Maximum Quiescent Supply Current (per Package)	V_{IN} = V_{CC} or GND I_{OUT} = 0 μA	I_{CC}	6.0	4.0	40	160	μA

8. Information on typical parametric values, along with high frequency or heavy load considerations, can be found in the ON Semiconductor High−Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns)

Parameter	Symbol	V_{CC} V	Guaranteed Limit			Unit
			−55°C to 25°C	≤85°C	≤125°C	
Maximum Clock Frequency (50% Duty Cycle) (Figures 4 and 7)	f_{max}	2.0 4.5 6.0	6.0 30 35	4.8 24 28	4.0 20 24	MHz
Maximum Propagation Delay, Clock to Q (Figures 5 and 7)	t_{PLH} t_{PHL}	2.0 4.5 6.0	110 22 19	140 28 24	165 33 28	ns
Maximum Propagation Delay, Reset to Q (Figures 2 and 7)	t_{PLH} t_{PHL}	2.0 4.5 6.0	110 21 19	140 28 24	160 32 27	ns
Maximum Output Transition Time, Any Output (Figures 4 and 7)	t_{TLH} t_{THL}	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
Maximum Input Capacitance	C_{in}		10	10	10	pF
		Typical @ 25°C, V_{CC} = 5.0 V				
Power Dissipation Capacitance, per Enabled Output (Note 10)	C_{PD}	62				pF

9. For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High−Speed CMOS Data Book (DL129/D).
10. Used to determine the no−load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see the ON Semiconductor High−Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (C_L = 50 pF, Input $t_r = t_f$ = 6.0 ns)

Parameter	Figure	Symbol	V_{CC} V	Guaranteed Limit						Unit
				−55°C to 25°C		≤85°C		≤125°C		
				Min	Max	Min	Max	Min	Max	
Minimum Setup Time, Data to Clock	6	t_{su}	2.0 4.5 6.0	50 10 9.0		65 13 11		75 15 13		ns
Minimum Hold Time, Clock to Data	6	t_h	2.0 4.5 6.0	5.0 5.0 5.0		5.0 5.0 5.0		5.0 5.0 5.0		ns
Minimum Recovery Time, Reset Inactive to Clock	5	t_{rec}	2.0 4.5 6.0	5.0 5.0 5.0		5.0 5.0 5.0		5.0 5.0 5.0		ns
Minimum Pulse Width, Clock	4	t_w	2.0 4.5 6.0	75 15 13		95 19 16		110 22 19		ns
Minimum Pulse Width, Reset	5	t_w	2.0 4.5 6.0	75 15 13		95 19 16		110 22 19		ns
Maximum Input Rise and Fall Times	4	t_r, t_f	2.0 4.5 6.0		1000 500 400		1000 500 400		1000 500 400	ns

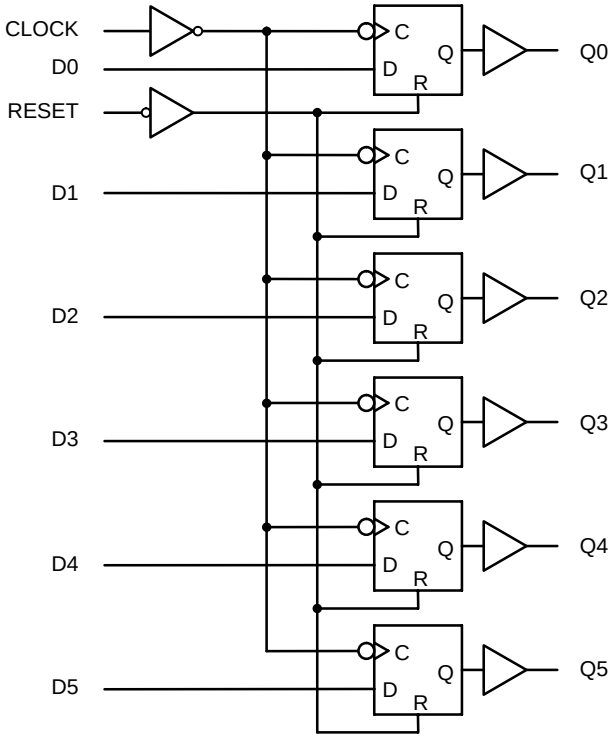


Figure 3. Expanded Logic Diagram

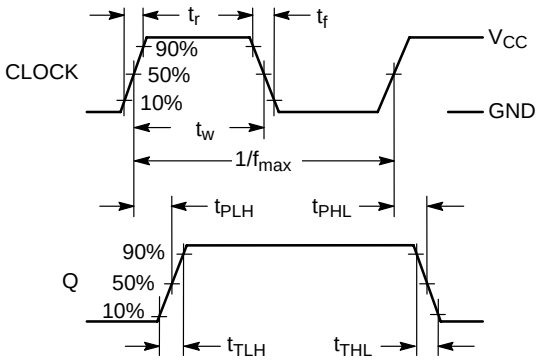


Figure 4. Switching Waveform

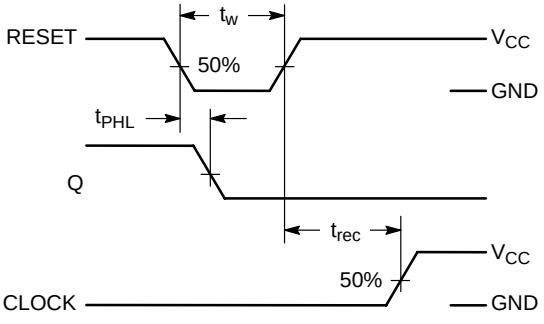


Figure 5. Switching Waveform

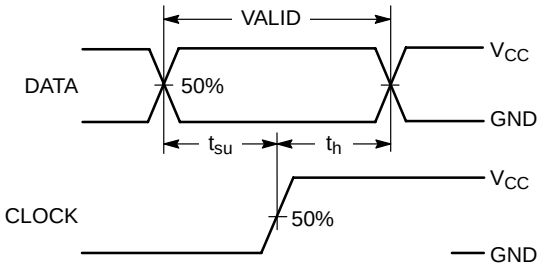
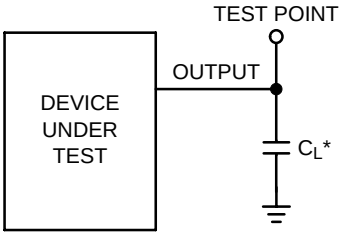


Figure 6. Switching Waveform



*Includes all probe and jig capacitance

Figure 7. Test Circuit

PIN1/PRODUCT ORIENTATION CARRIER TAPE

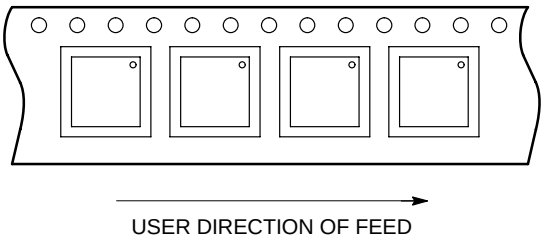


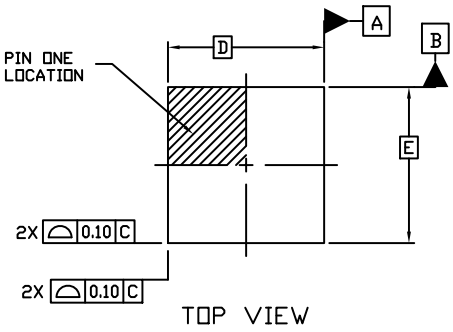
Figure 8.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

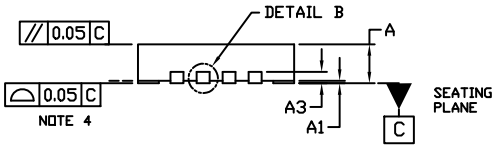
QFN16 3x3, 0.5P
CASE 485G
ISSUE G

DATE 08 OCT 2021

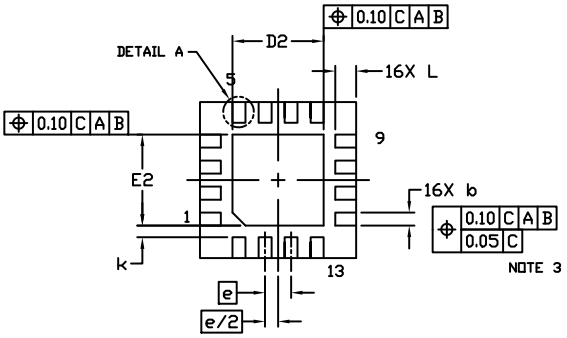
SCALE 2:1



TOP VIEW

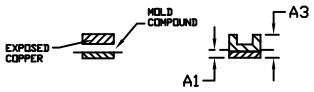


SIDE VIEW

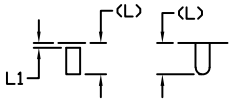


BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.



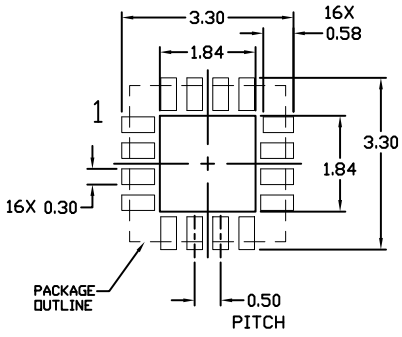
DETAIL B
ALTERNATE CONSTRUCTIONS



DETAIL A
ALTERNATE TERMINAL CONSTRUCTIONS

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	0.80	0.90	1.00
A1	0.00	0.03	0.05
A3		0.20 REF	
b	0.18	0.24	0.30
D		3.00 BSC	
D2	1.65	1.75	1.85
E		3.00 BSC	
E2	1.65	1.75	1.85
e		0.50 BSC	
k		0.18 TYP	
L	0.30	0.40	0.50
L1	0.00	0.08	0.15

MOUNTING FOOTPRINT



GENERIC MARKING DIAGRAM*

XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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